FP7 - ICT Work Programme 2011-12

Objective 3.1

"Very advanced Nanoelectronic components: design, engineering, technology and manufacturability"

Isabel Vergara

European Commission Information Society & Media Directorate-General Nanoelectronics



NCP, 13th May 2011, Brussels.



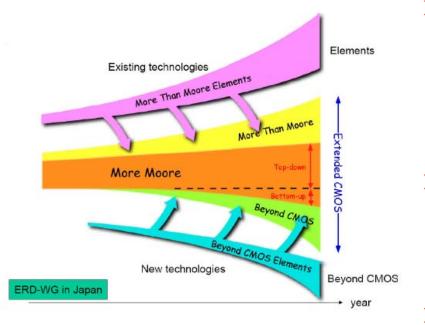
Presentation Outline

- Objective 3.1:
 - What are we looking for?
 - General concepts
 - Target outcomes
 - What do we not want?
- Related Objectives or Programmes
- Key groups / Leading players
- Additional background documents





What are we looking for?



ITRS-ERD vision of the role of Beyond CMOS and More than Moore elements to form future extended CMOS platforms (2010).

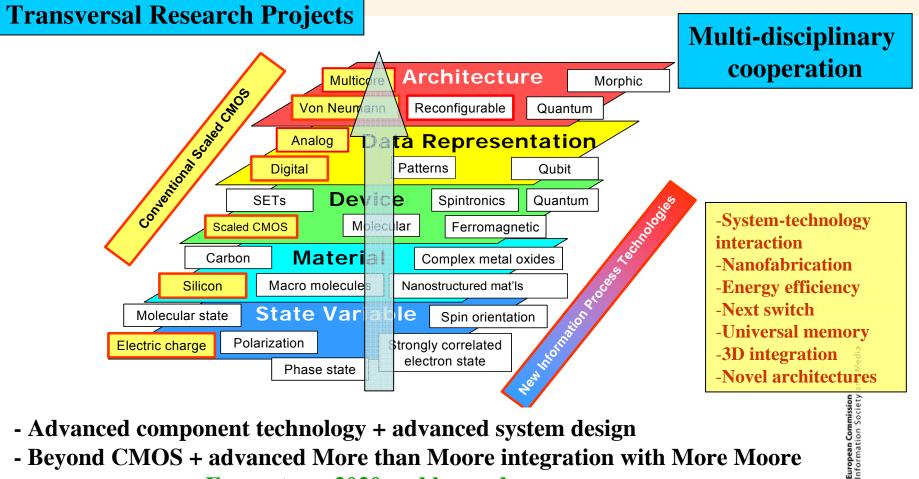




- New advanced nanoelectronic components based on "beyond CMOS devices" and their integration with advanced More than Moore elements and with existing and new nano-CMOS to support miniaturised electronic and communication technologies for 2020 and beyond.
- Improved technology, engineering, nanomanufacturing and design solutions for increased performance, increased systemability, integratability and manufacturability.
- Joint equipment assessment and broker services to facilitate access to world wide market for SMEs and academics.



Work Programme 2011-12 General concepts



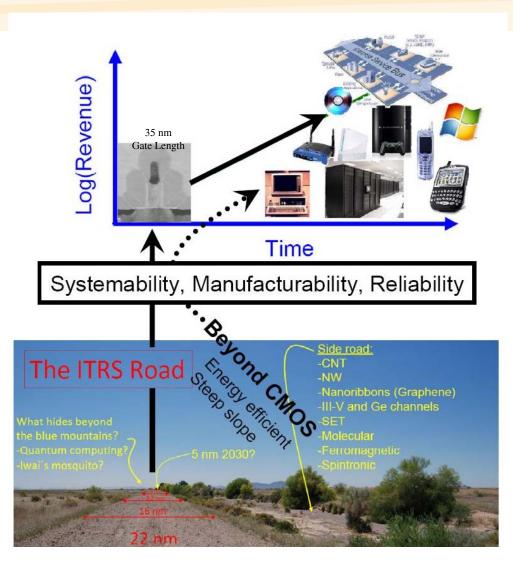
- Advanced component technology + advanced system design
- Beyond CMOS + advanced More than Moore integration with More Moore For systems 2020 and beyond

Systemability, integratability, manufacturability

Objective 3.1: Advanced Nanoelectronics Technology

- To stimulate interaction of system and technology to better explore European system competences.
- To address energy efficiency needs for mobile applications
- Nanoelectronics products as system enablers and solution providers for global challenges as aging society, global warming, growing population or sustainable manufacturing.
- To prepare for "beyond" traditional shrinking (ITRS roadmap)





Objective 3.1 *Manufacturing and Equipment assessment*

- Access to nano-manufacturing and to advanced technologies to be assured in Europe.
- Access to world wide equipment market for European suppliers, especially SMEs, need to be stimulated.



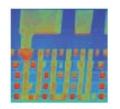
Semiconductor Equipment for Wafer Bonding with Plasma Activation EV Group, CEA-LETI, Soitec



Ruthenium Atomic Vapor Deposition Competitiveness in Nanoelectronic Device Generations AIXTRON, Fraunhofer IISB, Infineon Munich



Low Energy and Dose Implant Test SEMILAB, Fraunhofer IISB, ST Microelectronics Crolles II, NXP Crolles R&D



Metrology Using X-Ray Techniques Jordan Valley, CEA-LETI, STMicroelectronics Crolles II, NXP Crolles R&D



3D Integration of Bulk Si Wafers EV Group, CEA-LETI, STMicroelectronics Crolles II

ICT Work Programme 2011-12 Nanoelectronics

Objective 3.1: Very Advanced Nanoelectronics Components

Call 8

60M€

SEVENTH FR

a) Beyond CMOS technology	STREPs		
b) Circuit-technology solutions	STREPs and at least 1 IP	55 M€	
c) Nano-manufacturing and Joint Equipment Assessment	STREPs and at least 1 IP		n y and Media
d) Coordination and Support Actions	CSAs	5 M€	European Commission
AM ENDERK		00000	1.

a) Beyond CMOS technology

- New switches and interconnects (scalability, performance and energy efficiency gains, operational reliability and RT operation);
- Advanced system integration technology and new methods for computation;
- Emerging memories targeting the concept of non-volatile universal memory;
- Nano-photonic devices & interconnects integrated with nano- and Beyond-CMOS
- Carbon based electronic devices;
- Novel materials for interconnects , nano-packaging, Beyond-CMOS (logic and memory);
- Understanding fundamental artefacts and limits: nano-scale thermal processes; computational material and device science.

Developed components and technologies need to fulfil the criteria of "systemability", "integratability", and "manufacturability".



ind Media

Funding schemes:

IP

STREPs

b) Circuit-technology solutions

- Architectures including energy efficiency, spin devices; silicon with molecular switches; ferromagnetic logic; heterogeneous and morphic system architectures.
- Circuit design methodologies and tools
- Technology addressing e.g. device leakage current, power dissipation, ... monolithic as well as 3D integration of Beyond CMOS and advanced MtM.
- Modelling and simulation
- Design-technology solutions for energy efficiency, high reliability and robustness.

Developed components and technologies need to fulfil the criteria of "systemability", "integratability", and "manufacturability".

The interaction of circuit, device and technology research communities will be stimulated

c) Nano-manufacturing and joint equipment assessment

- Manufacturing approaches to Beyond-CMOS and advanced MtM, and to their integration with nanoCMOS including 3D integration.
- Enhanced variability control; integrated metrology/inspection/analysis concepts and tools to support 3D approaches; functionalised assembly and packaging.
- Joint assessments of (combined) equipment/metrology/process solutions ranging from proof of concept for "disruptive" approaches and for 450mm to prototype testing with suppliers and users.
- 200/300 mm wafer integration platforms and short user-supplier feedback loops.

Comprising the complete manufacturing supply chain for flexible and customised manufacturing of integrated nano- and Beyond-CMOS components Funding schemes: IP STREPs

nd Media

d) Support measures

- Broker services to offer European researchers and SMEs access to training, to CAD tools and to advanced technologies, design kits and IP blocks for education, prototyping and small volume production.
- Roadmaps; benchmarks; strategy papers; studies of limits of Beyond-CMOS and advanced MtM processes, devices and architectures.
- Stimulation of young people towards electronics careers.
- International cooperation (USA, Taiwan, Korea, Japan)
- Support, coordination and standardisation actions including preparatory work for 450mm wafer processing targeting material and equipment companies









and Media

3.1 Very advanced nanoelectronic components: design, engineering, technology and manufacturability **Expected Impact**

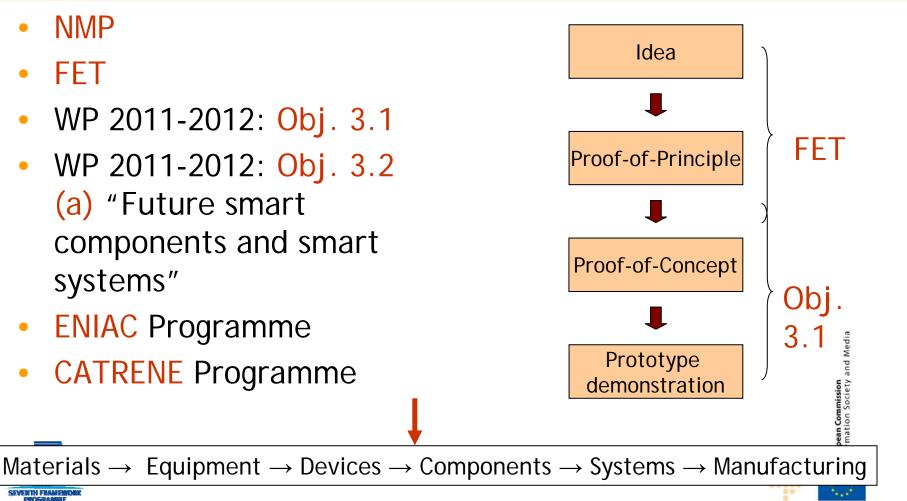
- Increased European knowledge, resources and skills at the frontier of nanoelectronics technology and miniaturised electronic systems, enabling further European partnerships in ww collaborations. European research organisations in leading positions.
- A more integrated nanoelectronics technology, device and design research community, better targeted to the business strategy of the European industry.
- Increased attractiveness for investments in components miniaturisation, \succ functionalisation and manufacturing in Europe; increased business opportunities and market share.
- New electronic applications of high economic and socio-economic \succ relevance
- Commission ion Society and Media Strengthened competitiveness of the European foodchain for the न anoelectronics industry (materials, equipment and components supplie 🎉 ____academia and institutes).

Related Objectives or Programmes

- NMP
- FET

SEVENTH FRAMEMO PROGRAMME

- WP 2011-2012: Obj. 3.1
- WP 2011-2012: Obj. 3.2 (a) "Future smart components and smart systems"
- **ENIAC** Programme •
- **CATRENE** Programme



What do we not want?

 <u>We want</u> very Advanced and Multidisciplinary Research, but

We do not want

- Research on components and technologies that do not investigate the need to fulfil the criteria of "systemability", "integratability" and "manufacturability", where appropriate.
- Research focused on materials
- Research focused on the development of equipment
- Research focused on large systems integration





Key groups / Leading players

Key Groups

- International Roadmap of Semiconductors (ITRS - ERD)
- Scientific Council of ENIAC
 ETP
- NANOTEC CA Building a Nanoelectronics Design and Technology Community (https://www.fp7nanotec.eu/)
- ENI2 Nanoelectronics Infrastructure (http://www.sinano.eu/sinano /projects/eni2.html)

Leading Players

- Leading companies (ST, INTEL, Global Foundries, Infineon, IBM, NXP, Numonyx, ...)
- Leading Regional clusters (Dresden - GF/Fraunhofer; Grenoble - CEA/ST Leuven -IMEC...) and SMEs around them.
- RTO European Universities
 of Excellence



Additional/background documents

- FP7 Workshop on Advanced Nanoelectronics Technologies (<u>ftp://ftp.cordis.europa.eu/pub/fp7/ict/docs/nanoelectronics/01</u> <u>1209-wshop-rep-ai-v7b-clean_en.pdf</u>)
- Workshop on Manufacturing of Beyond CMOS and Advanced More than Moore Devices

(http://cordis.europa.eu/fp7/ict/nanoelectronics/element s/wshop-report-v6-fin-070211.pdf)





and Media

> Call 8

- Open: 26 July 2011
 - Close: 17 January 2012 (at 17:00 Brussels local time)

Funding schemes:

- a) Beyond CMOS technology: STREPs
- b) Circuit-technology solutions: STREPs and at least 1 IP
- c) Nano-manufacturing and joint equipment assessment: STREPs and at least 1 IP
- d) Support measures: CSAs
- Indicative budget distribution 60 M€:
 - IP/STREP 55 M€
 - CSA 5 M€





Thank you

Information Society and Media: http://ec.europa.eu/information_society http://cordis.europa.eu/fp7/ict/nanoelectronics/mission_en.html

European research on the web: http://cordis.europa.eu http://www.eniac.eu

Contact:

Isabel.vergara-ogando@ec.europa.eu





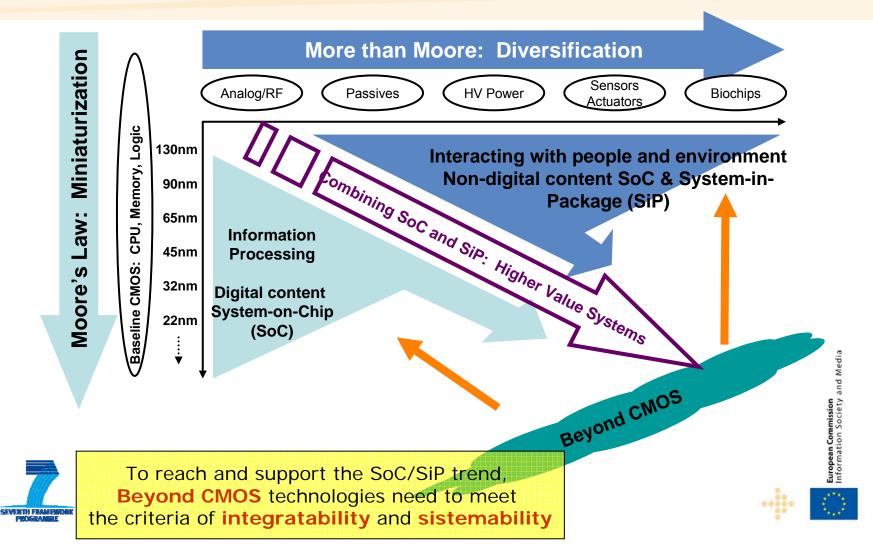
Nanoelectronics in FP7

- FP7 ICT Call 1 (2007): Next-generation Nanoelectronics Components and Electronics Integration. 86 M€
- FP7 ICT Call 4 (2008): Design of Semiconductor Components and Electronic Based Miniaturised Systems. 25 M€
- FP7 ICT Call 5 (2009): Nanoelectronics Technology. 35 M€
- FP7 ICT Call 7 (2010): Smart Components and Smart Systems Integration. 38M€
- FP7 ICT Call 8 (2011): Very Advanced Nanoelectronics Components. 60 M€

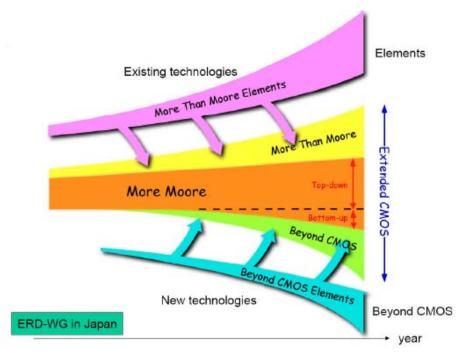




Introduction European vision of the More Moore and More than Moore domains



Objective 3.1: Advanced Nanoelectronics Technology



ITRS-ERD vision of the role of Beyond CMOS and More than Moore elements to form future extended CMOS platforms.



- Future developments in Beyond CMOS and More than Moore as an extended-CMOS vision. No disconnection from the advanced silicon CMOS in order to keep impact of its results on the applications and markets.
- Needs of hybridizing silicon with molecular switches, ferromagnetic logic, spin devices and sensors in order to enable heterogeneous and morphic system architectures.
- Integrate-ability of novel technology with CMOS and their reliability become key factors.